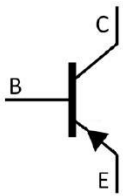


Silicon PNP transistor in a TO-220F Plastic Package.

Low $V_{CE(sat)}$, High P_C , complementary pair with 2SD2012.

Audio frequency power amplifier applications.

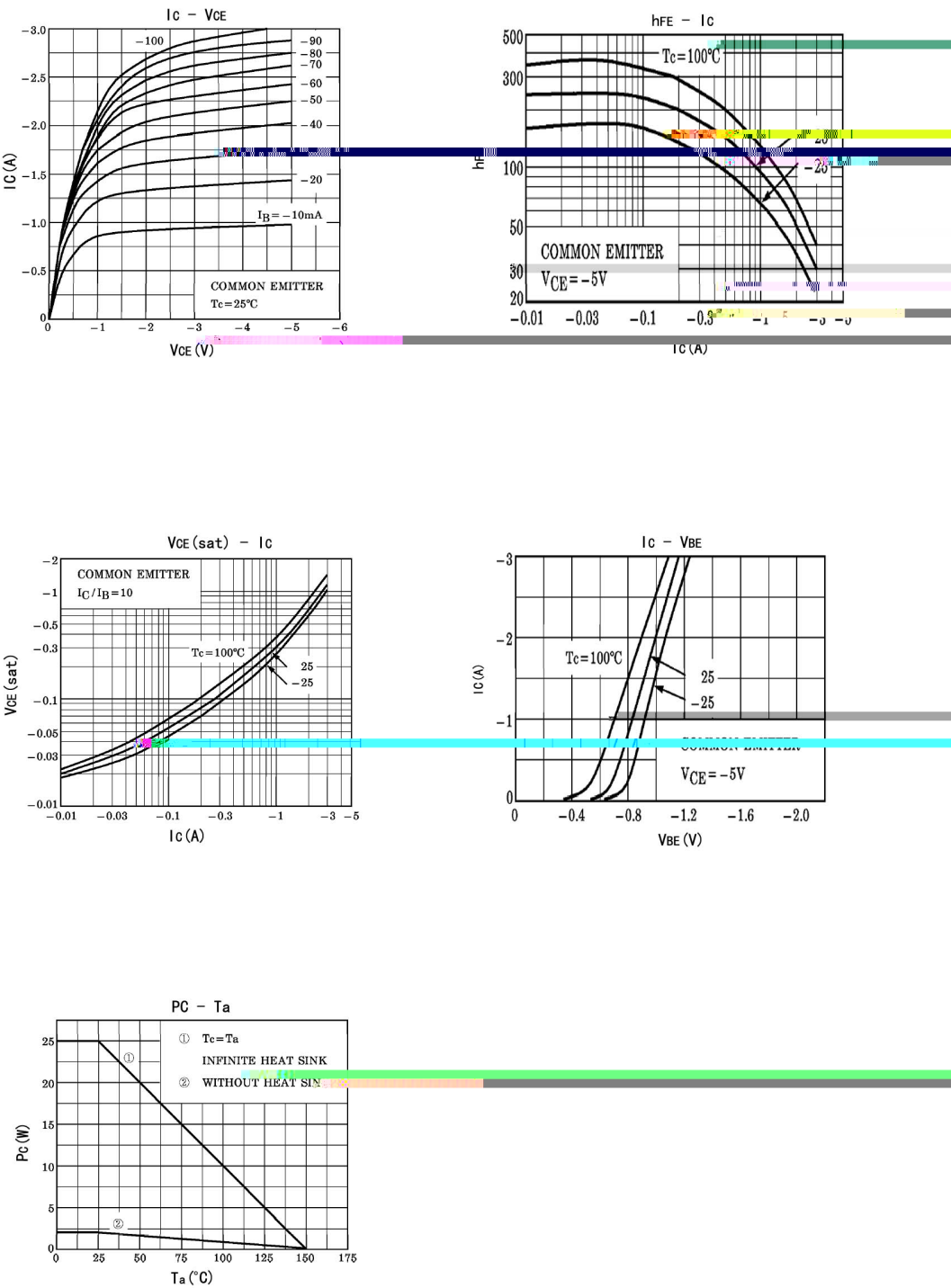


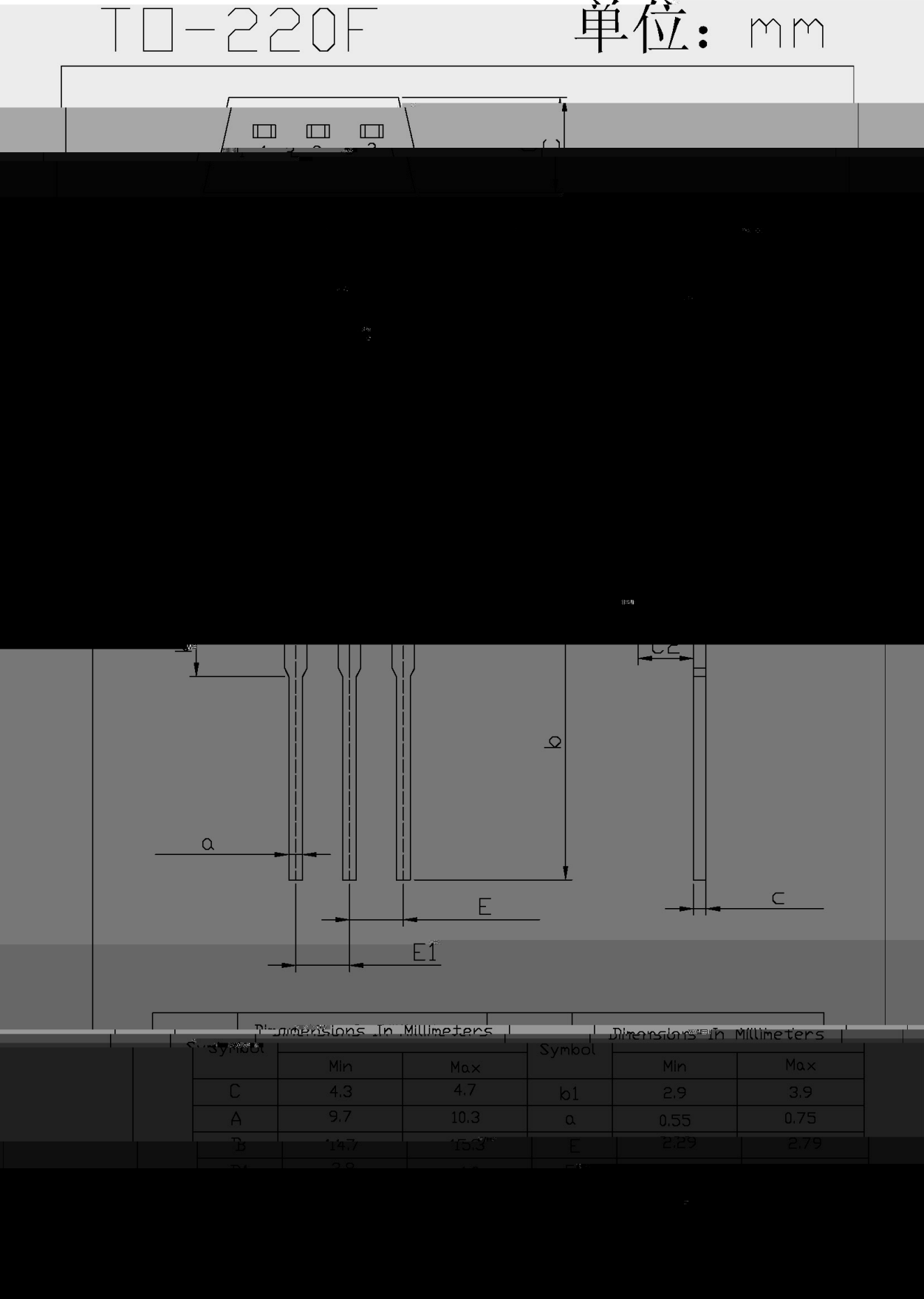
PIN1 Base PIN 2 Collector PIN 3 Emitter

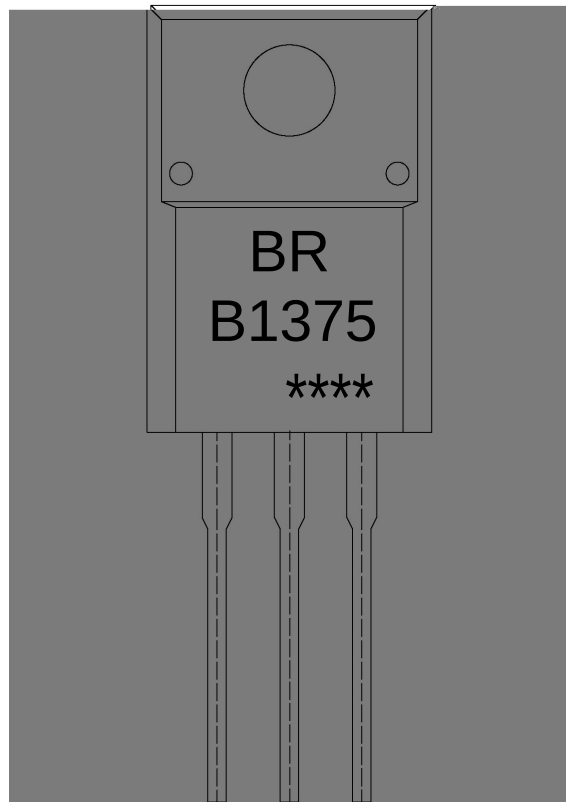
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current	I_B	-0.5	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C (T_c=25^{\circ}\text{C})$	25	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60\text{V}$ $I_E=0$			-10	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}				





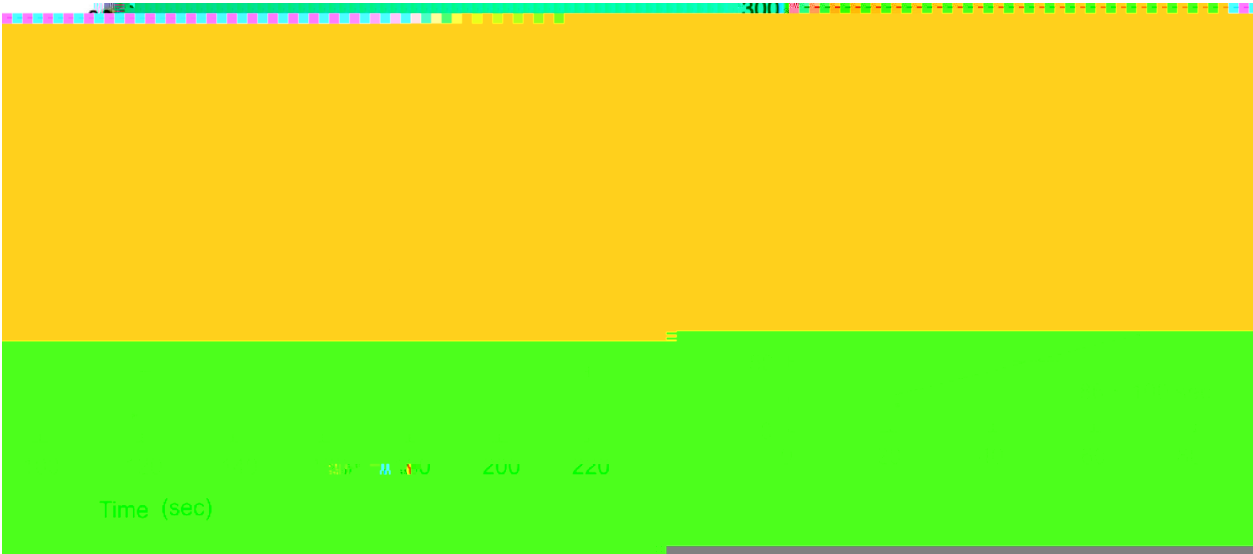


Note:

BR: Company Code.

B1375: Product Type.

****: Lot No. Code, code change with Lot No.



				Note:
1	25	150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255	5	5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3		2 10	/sec.	3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec. Temp.:270±5℃ Time:10±1 sec

/ BULK

Package Type	Units		Dimension	(unit mm ³)
	Units/Bag	Bags/Inner Box		